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(Use several sheets if necessary)

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Docket Number (Optional)	Application Number
BUR920000029[redacted]1	09/713,830
Applicant(s)	
Furukawa et al.	
Filing Date	**Group Art Unit**
11/15/2000	2826

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	CITE NO	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
KV	AA	5,650,342	7/22/1997	Satoh et al.	437	36	Oct 30, 1992
KV	AB	5,650,343	7/22/1997	Luning et al.	437	36	Jun 7, 1995
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FOREIGN PATENT DOCUMENTS

	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation YES	Translation NO
KV	AD	JP10294453A2	04/17/1997	Japan	H01L	29/78	✓	
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OTHER DOCUMENTS *(Including Author, Title, Date, Pertinent Pages, Etc.)*

KV	AF	"Well-controlled, selectively under-etched Si/SiGe gates for RF and high performance CMOS" T. Skotnicki et al., 2000 Symposium on VLSI Technology Digest of Technical Papers, 2000 IEEE, pp. 156-157
KV	AG	PCT International Search Report

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EXAMINER	DATE CONSIDERED
Kevin Quinto	12/22/02

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